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Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 80 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	80 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V			
V <sub>TM</sub> (typ.)	1.16 V			
I <sub>GT</sub>	100 mA			
T <sub>J</sub>	-40 °C to +150 °C			
Package	TO-247AD 3L			
Circuit configuration	Single SCR			

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

### **DESCRIPTION**

The VS-80TPS16L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V	
On-state voltage	V <sub>T</sub>	80 A, T <sub>J</sub> = 125 °C, typical	1.16	V	
Average rectified forward current	I <sub>T(AV)</sub>		80		
Maximum continuous RMS on-state current	I <sub>RMS</sub>		126	Α	
Non-repetitive peak surge current	I <sub>TSM</sub>		1000		
Maximum rate of rise	dV/dt		1000	V/µs	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C	

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-80TPS16L-M3	1600	1700	10



PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 113 °C, 180° conduction half sine v	vave	-	80	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	126	Α
Peak, one-cycle non-repetitive surge current	<b>L</b>	10 ms sine pulse, rated $V_{\mbox{\scriptsize RRM}}$ applied		-	840	
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial T <sub>J</sub> =	-	1000	
I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	T <sub>J</sub> maximum	-	3536	A <sup>2</sup> s
1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		-	5000	A <sup>2</sup> s
I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	d, T <sub>J</sub> = 125 °C	-	50 000	A²√s
		80 A, T <sub>J</sub> = 25 °C		1.22	1.40	V
	V <sub>T</sub>	160 A, T <sub>J</sub> = 25 °C		1.48	1.66	
On-state voltage		80 A, T <sub>J</sub> = 125 °C		1.16	1.24	
		160 A, T <sub>J</sub> = 125 °C		1.49	1.62	
Low level value of threshold voltage	V <sub>T01</sub>	T 450 00		-	0.80	V
High level value of threshold voltage	V <sub>T02</sub>	T <sub>J</sub> = 150 °C		-	0.89	v
Low level value of on-state slope resistance	r <sub>t1</sub>	T 150 °C		-	4.82	0
High level value of on-state slope resistance	r <sub>t2</sub>	T <sub>J</sub> = 150 °C		-	4.51	mΩ
Rate of rise of turned-on current	dl/dt	$T_J$ = 125 °C, $V_R$ = 1000 V, $I_T$ = 100 A, $I_{gt}$ = 450 mA, $V_{GT}$ = 2.5 V		-	500	A/µs
Holding current	I <sub>H</sub>	$\frac{I_{H}}{I_{L}}$ Anode supply = 6 V, resistive load, $T_{J} = 25  ^{\circ}\text{C}$		-	200	A
Latching current	ΙL			-	400	mA
Deverse and direct leakage augrent	l/l	T <sub>J</sub> = 25 °C		50	200	μΑ
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			60	mA
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , I	R <sub>g</sub> -k = open	-	1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	$P_{GM}$	10 ms sino puls	40		10	W
Average gate power	P <sub>G(AV)</sub>	To this sine puis	10 ms sine pulse, no voltage reapplied			
Peak gate current	I <sub>GM</sub>				2.5	Α
Peak negative gate voltage	-V <sub>GM</sub>			-	10	V
Required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C Anode supply = 6 V resistive load		1	1.5	V
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C Anode supply = 6 V resistive load		-	100	mA
DC gate voltage not to trigger	$V_{GD}$	T 105 °C V 20 0/ reted value		-	0.20	٧
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = 80 % rated value			5	mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_T$ = 80 A, $V_D$ = 50 % $V_{DRM}$ , $I_{gt}$ = 300 mA, $T_J$ = 25 °C	2	-	
Turn-off time	t <sub>q</sub>	$I_T$ = 80 A, $V_D$ = 80 % $V_{DRM}$ , $dV/dt$ = 20 $V/\mu s$ , $t_p$ = 200 $\mu s$ $I_{gt}$ = 100 mA, $dI/dt$ = 10 $A/\mu s$ , $V_R$ = 100 $V$ , $T_J$ = 150 °C	150	-	μs



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS
Maximum operating junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C
Maximum thermal resistance, junction to case		R <sub>thJC</sub>		-	0.23	
Maximum thermal resistance, junction to ambient		$R_{thJA}$		-	40	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.	20	
Approximate weight				6 (0	.21)	g (oz.)
Mounting torque	minimum			6	(5)	kgf · cm
Mounting torque	maximum			12	(10)	(lbf · in)
Marking device			Case style TO-247AD 3L		80TPS1	6L

△R <sub>thJ-HS</sub> CONDUCTION PER JUNCTION											
DEVICE	s	SINE HALF-WAVE CONDUCTION				RECTANGULAR WAVE CONDUCTION				UNITS	
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-80TPS16L-M3	0.031	0.036	0.040	0.042	0.044	0.028	0.036	0.038	0.040	0.042	°C/W

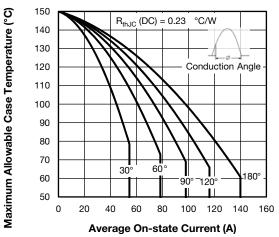


Fig. 1 - Current Rating Characteristics

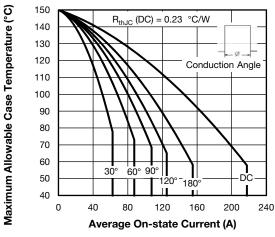


Fig. 2 - Current Rating Characteristics

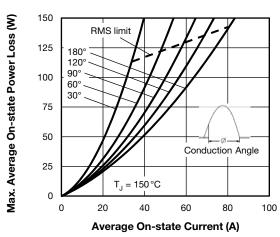


Fig. 3 - On-State Power Loss Characteristics

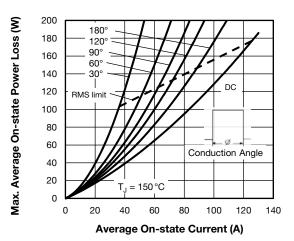


Fig. 4 - On-State Power Loss Characteristics



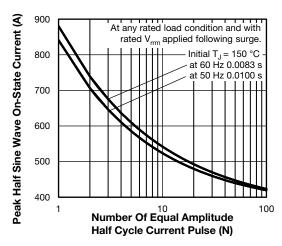


Fig. 5 - Maximum Non-Repetitive Surge Current

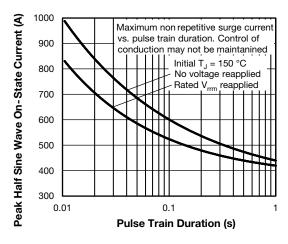


Fig. 6 - Maximum Non-Repetitive Surge Current

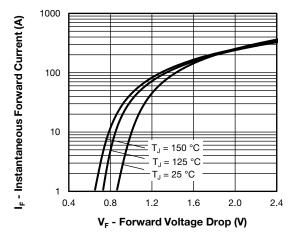


Fig. 7 - On-State Voltage Drop Characteristics

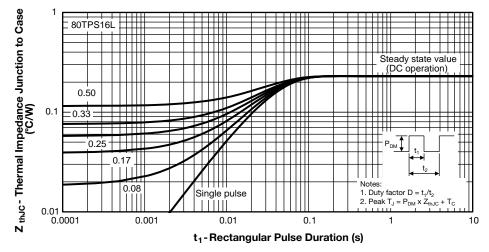
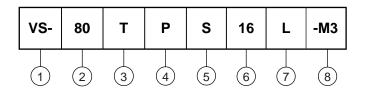


Fig. 8 - Maximum Thermal Impedance ZthJC Characteristics



### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code (80 = 80 A)

- Circuit configuration:

T = thyristor

**4** - P = TO-247 package

5 - Type of silicon:

S = standard recovery rectifier

**6** - Voltage code (16 = 1600 V)

7 - Package L = long lead

- -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

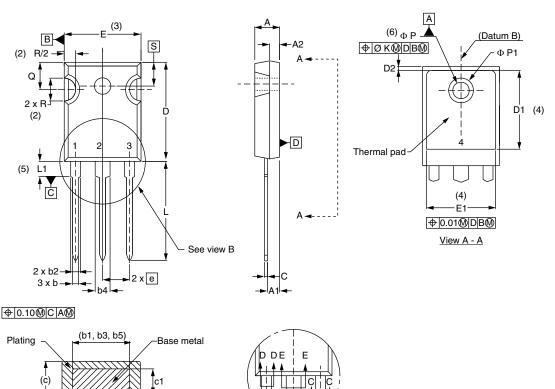
ORDERING INFORMATION (example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-80TPS16L-M3	25	500	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS		
Dimensions <u>www.vishay.com/doc?95626</u>		
Part marking information	www.vishay.com/doc?95007	



# **TO-247AD 3L**

### **DIMENSIONS** in millimeters and inches



		Section C -	C, D - D, E -	<u>· E</u>	
SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	

0.039

0.065

0.065

0.102

0.102

0.015

0.015

0.776

0.515

0.053

0.094

0.092

0.135

0.133

0.035

0.033

0.815

(h h2 h4)

:5	

View B

SYMBOL	MILLIMILILIA		INOTILS		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØΚ	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		
•	•		•		•

INCHES

MILLIMETERS

### Notes

b1

b2

b3

b4

b5

С

с1

D

D1

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

1.35

2.39

2.34

3.43

3.38

0.89

0.84

20.70

- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

3

- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1

0.99

1.65

1.65

2.59

2.59

0.38

0.38

19.71

13.08

- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



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